

## Silicon NPN Power Transistors

2SC1619

**DESCRIPTION**

- With TO-3 package
- High current capacity
- Wide safe operating area

**APPLICATIONS**

- For audio frequency output applications

**PINNING(see fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

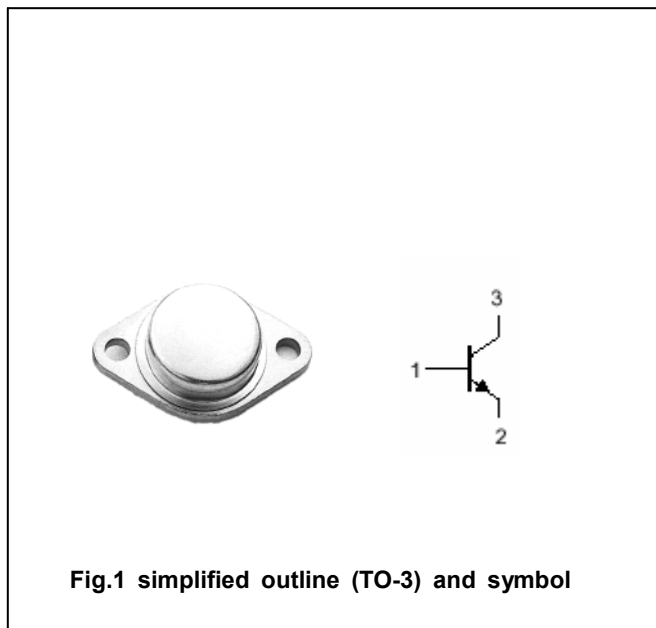


Fig.1 simplified outline (TO-3) and symbol

**ABSOLUTE MAXIMUM RATINGS(Ta=25℃)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	100	V
$V_{CEO}$	Collector-emitter voltage	Open base	80	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		6	A
$I_{CM}$	Collector current-peak		10	A
$P_C$	Collector power dissipation	$T_C=25^\circ\text{C}$	50	W
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA; I <sub>B</sub> =0	80			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.4 A			2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.4 A			2.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =100V; I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =3A ; V <sub>CE</sub> =4V	20		180	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =12V		10		MHz

PACKAGE OUTLINE

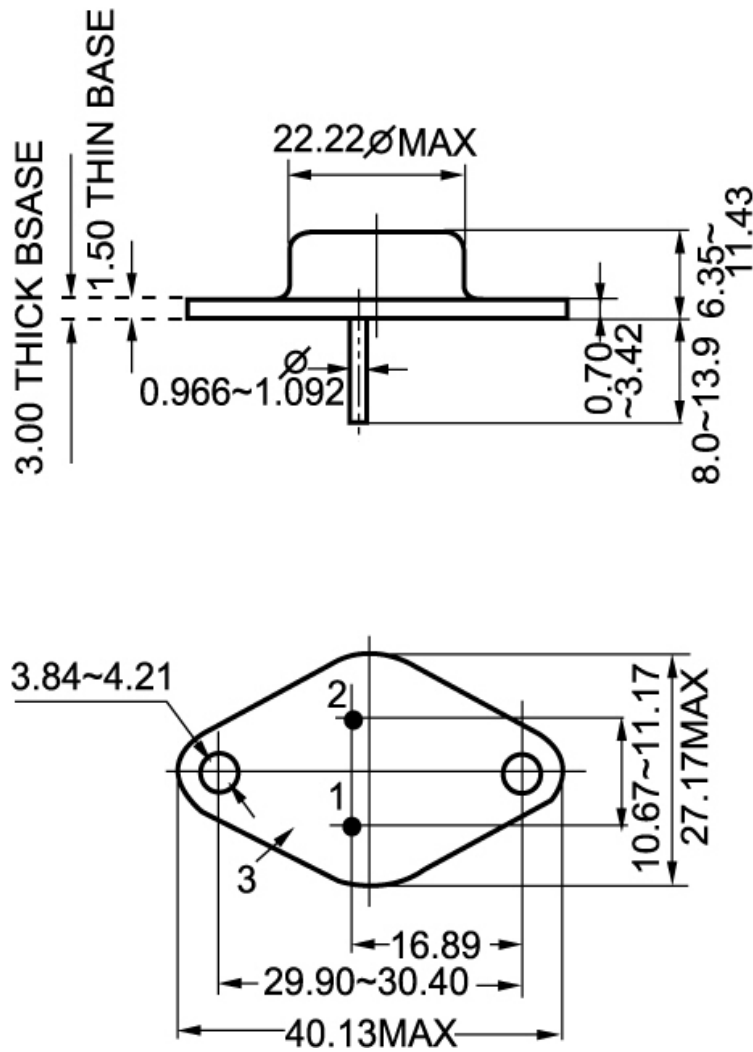


Fig.2 Outline dimensions